

200V N-Channel Enhancement-Mode Power MOSFET

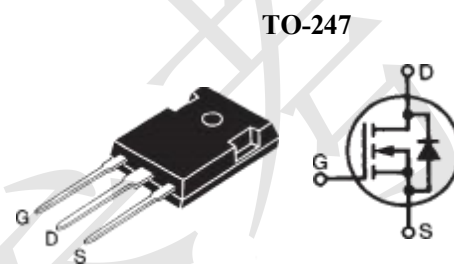
General Features

- Enhancement Mode
- Linear MOSFET
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- High Power Density
- RoHS Compliant
- Avalanche Rated

BV_{DSX}	$R_{DS(ON)} (Max.)$	$I_{DSS}(Min)$
200V	30mΩ	80A

Applications

- Suppressing Surge Current
- Start-up Circuits
- Converters
- Synchronous Rectification
- Constant Current Source
- Ramp Generators
- Current Regulators
- Protection Circuits
- Linear Amplifiers



Ordering Information

Part Number	Package	Marking	Remark
AKT84C20LA	TO-247	84C20LA	Halogen Free

Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	AKT84C20LA	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	200	V
V_{DGX}	Drain-to-Gate Voltage ^[1]	200	V
P_D	Power Dissipation	520	W
	Derating Factor above 25°C	520	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
T_L	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.